



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-100V	38mΩ@10V	-35A
	42mΩ@4.5V	

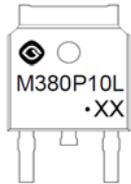
Feature

- Low Gate Charge
- Low RDS(on)
- 100% EAS Guaranteed

Application

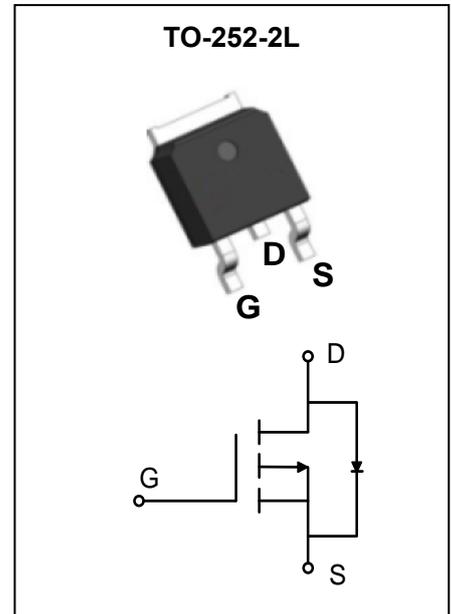
- Power Management Switch
- DC/DC Converter

MARKING:



M380P10L = Device Code

XX = Date Code



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	-100	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	-35	A
	$T_C = 100^\circ\text{C}$		-22	
Pulsed Drain Current ¹		I_{DM}	-140	A
Single Pulsed Avalanche Energy ²		E_{AS}	156.8	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	119	W
Thermal Resistance from Junction to Ambient ³		$R_{\theta JA}$	55	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	1.05	$^\circ\text{C}/\text{W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100V, V_{GS} = 0V$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 100^\circ\text{C}$		-100	
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.2	-1.7	-2.4	V
Drain-Source On-Resistance ⁴	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -20A$ $V_{GS} = -4.5V, I_D = -10A$		38	50	$m\Omega$
				42	58	
Forward Transconductance ⁴	g_{fs}	$V_{DS} = -10V, I_D = -20A$		44		S
Dynamic Characteristics⁵						
Input Capacitance	C_{iss}	$V_{DS} = -50V, V_{GS} = 0V, f = 1\text{MHz}$		5000		pF
Output Capacitance	C_{oss}			151		
Reverse Transfer Capacitance	C_{rss}			130		
Gate Resistance	R_g	$f = 1\text{MHz}$		11		Ω
Switching Characteristics⁵						
Total Gate Charge	Q_g	$V_{DS} = -50V, V_{GS} = -10V, I_D = -20A$		115		nC
Gate-Source Charge	Q_{gs}			15		
Gate-Drain Charge	Q_{gd}			14		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50V, V_{GS} = -10V, R_G = 3\Omega, I_D = -20A$		14.2		ns
Turn-On Rise Time	t_r			38.9		
Turn-Off Delay Time	$t_{d(off)}$			65		
Turn-Off Fall Time	t_f			37.5		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = -20A$			-1.2	V
Continuous Source Current	I_S	$T_C = 25^\circ\text{C}$			-35	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{A(MAX)}=150^\circ\text{C}$.
2. The test condition is $V_{DD} = -30V, L=0.4\text{mH}, I_{AS} = -28A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

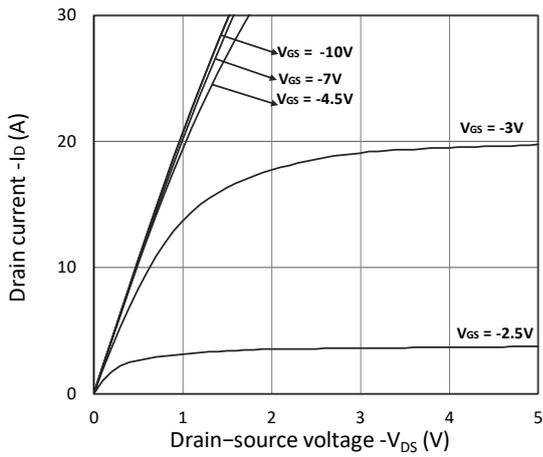


Figure 1. Output Characteristics

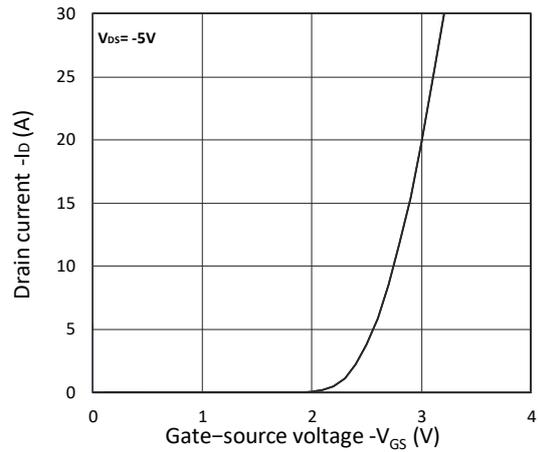


Figure 2. Transfer Characteristics

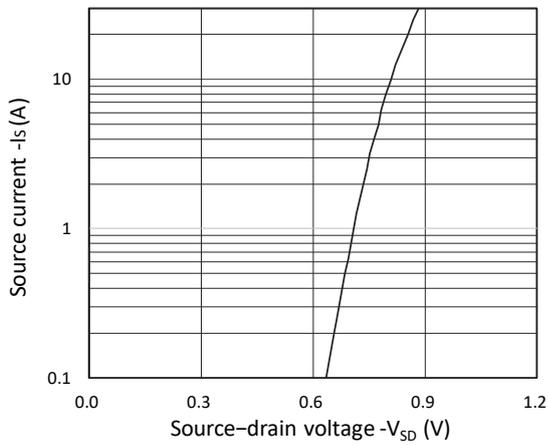


Figure 3. Forward Characteristics of Reverse

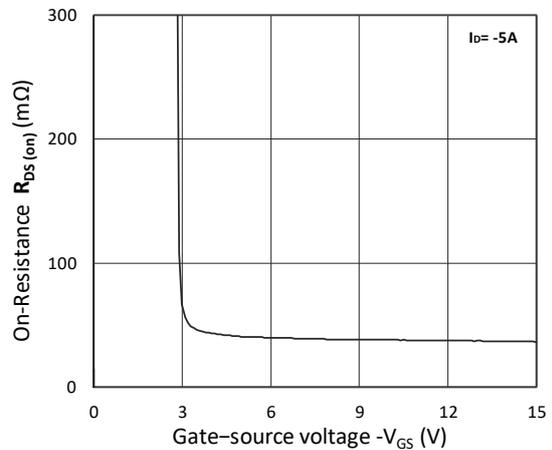


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

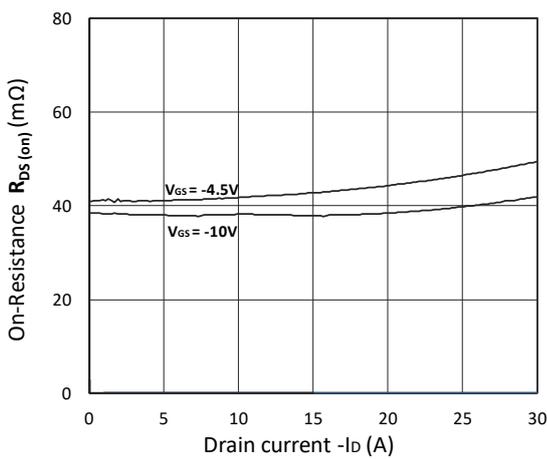


Figure 5. $R_{DS(ON)}$ vs. I_D

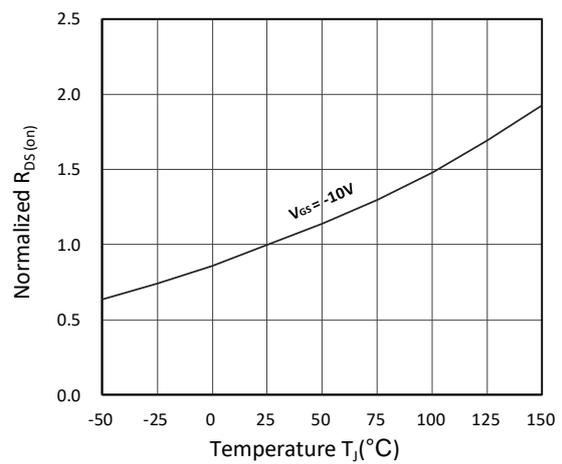


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

Typical Characteristics

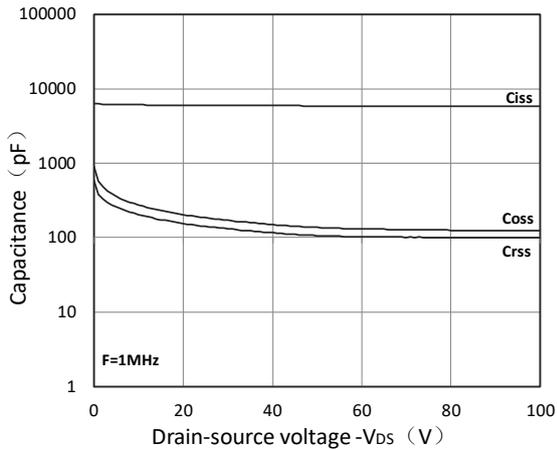


Figure 7. Capacitance Characteristics

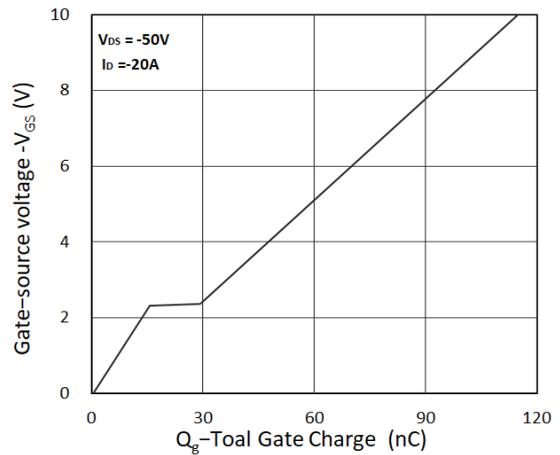


Figure 8. Gate Charge Characteristics

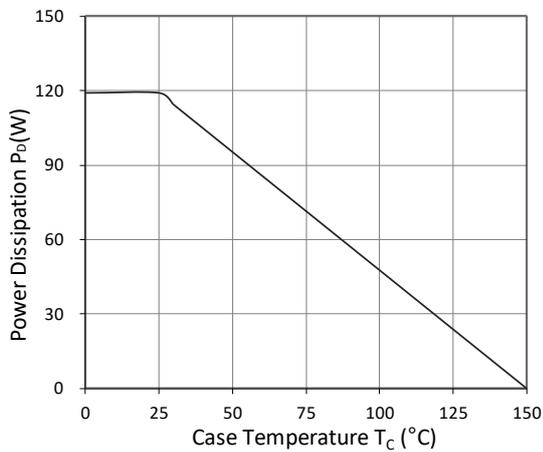


Figure 9. Power Dissipation

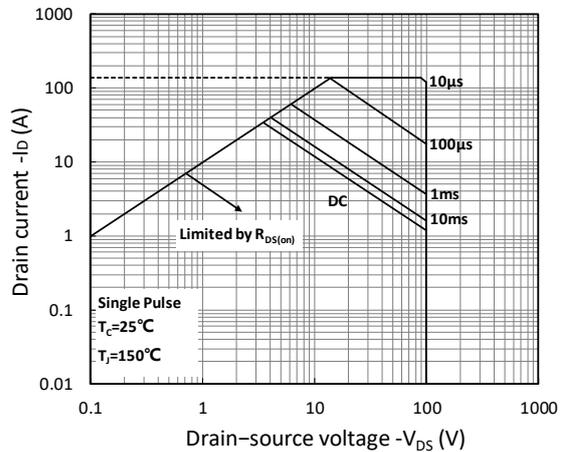


Figure 10. Safe Operating Area

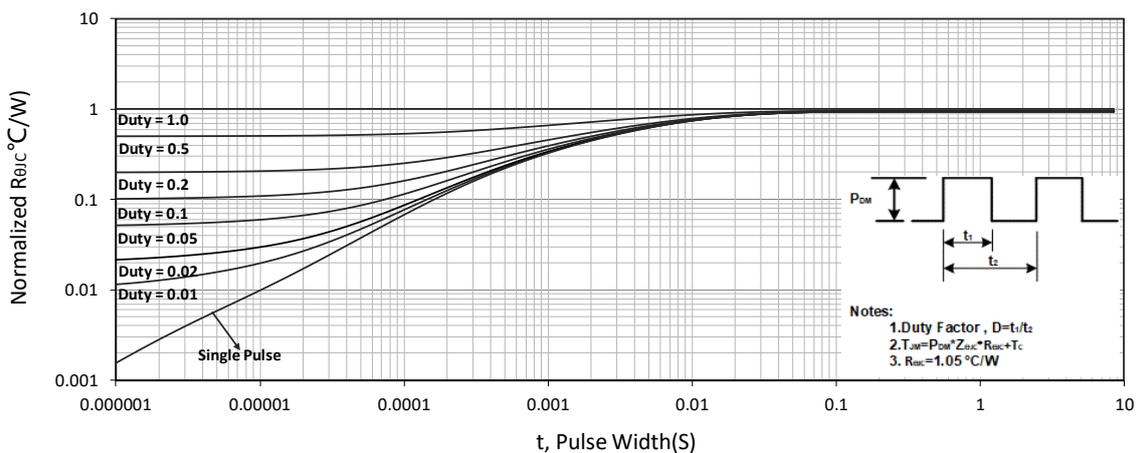
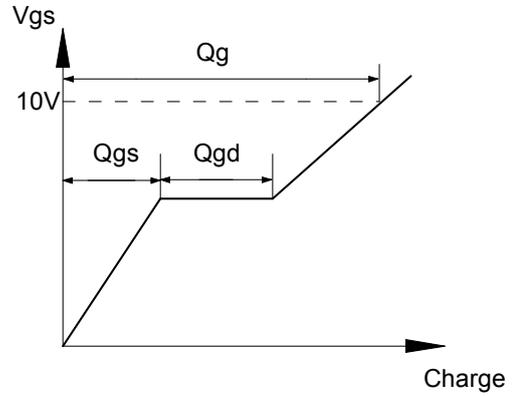
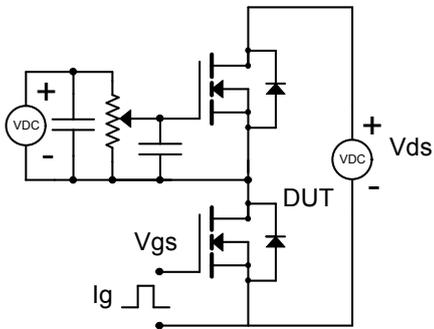
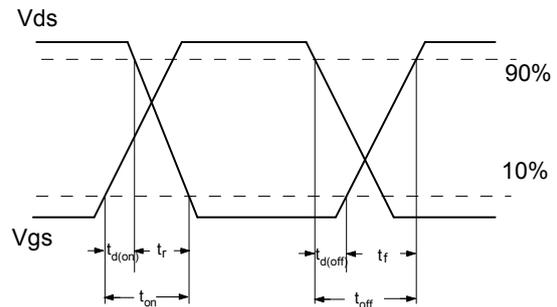
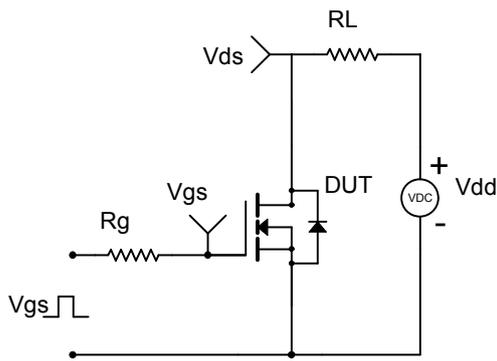


Figure 11. Normalized Maximum Transient Thermal Impedance

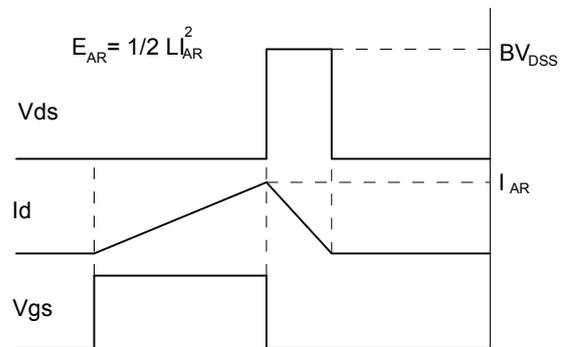
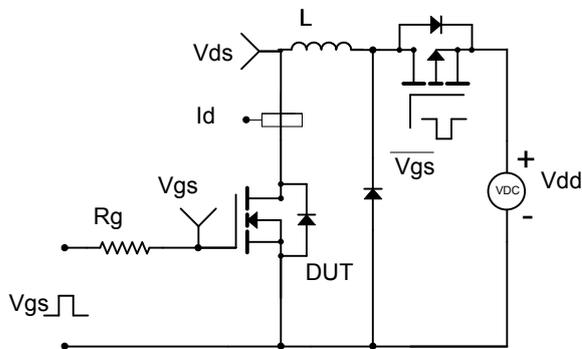
Gate Charge Test Circuit & Waveform



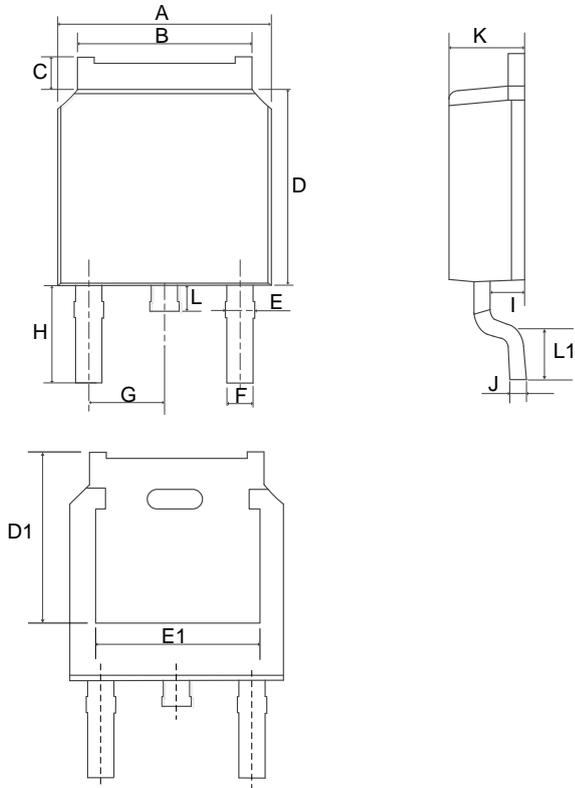
Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
D1	5.35REF	
E	0.68	1.10
E1	4.83REF	
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00
L1	1.50REF	

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.